

L Number	Hits	Search Text	DB	Time stamp
-	2	("6348705").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 08:11
-	13687	@ad<=20010508 and 'high dielectric constant'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 08:31
-	132	(@ad<=20010508 and 'high dielectric constant') and 'conductive barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:24
-	119	((@ad<=20010508 and 'high dielectric constant') and 'conductive barrier') and Al	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 08:24
-	77	((@ad<=20010508 and 'high dielectric constant') and 'conductive barrier') and Aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 08:25
-	3291	@ad<=20010508 and 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 08:33
-	79	(@ad<=20010508 and 'BST') and 'TiAlN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 13:41
-	39	((@ad<=20010508 and 'BST') and 'TiAlN') and aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 06:54
-	6626	((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 11:37
-	24	((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS.) and @ad<=20010508 and 'BST' and 'TiAlN' and 'metal layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 12:52
-	29173	@ad<=20010508 and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 12:05
-	30	(@ad<=20010508 and 'ferroelectric' ) and 'BST' and 'TiAlN' and 'metal layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/30 07:15
-	29	(@ad<=20010508 and 'ferroelectric' ) and 'BST' and 'TiAlN' and 'aluminum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 13:26
-	20	(@ad<=20010508 and 'ferroelectric' ) and 'capacitor' with 'BST' and 'TiAlN' and 'aluminum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 13:26

-	25	@ad<=20010508 and 'perovskite BST' or 'amorphous BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 15:09
-	3	@ad<=20010508 and 'amorphous BST' and conductive adj barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 13:06
-	569	(257/310).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 15:41
-	532	((257/310).CCLS.) and @ad<=20010508	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 13:56
-	11	(@ad<=20010508 and 'ferroelectric' ) and 'BST' and 'barrier' and 'aluminum layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/16 15:45
-	270	@ad<=19991222 and 'conductive barrier' and 'TiN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:52
-	566	((257/310).CCLS.) and @ad<=20010508	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:05
-	43	@ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:05
-	6	@ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST' and 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 15:02
-	2342	@ad<=19991222 and (257/295-296).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:15
-	795	@ad<=19991222 and (257/751).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:09
-	1232	@ad<=19991222 and (257/763-764).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:10
-	372	@ad<=19991222 and (257/303).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:11
-	1094	@ad<=19991222 and (257/306).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:12

-	479	@ad<=19991222 and (438/3).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:12
-	1072	@ad<=19991222 and (438/439-440).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:13
-	687	@ad<=19991222 and (438/687-688).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:21
-	4	(( "6294420" ) or ( "6365517" ) ).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:21
-	38	@ad<=19991222 and 'high dielectric constant' and 'conductive barrier' and 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 14:26
-	21	@ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST' and 'aluminum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/29 15:02
-	29	@ad<=19991222 and 'ferroelectric' and 'TiAlN' and 'metal layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:54
-	8	@ad<=19991222 and 'capacitor' with 'ferroelectric' with 'conductive diffusion barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:27
-	17	@ad<=19991222 and 'conductive barrier' and 'TiAlN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:52
-	5	@ad<=19991222 and 'BST' and 'conductive barrier' with 'TiAlN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 13:00
-	10	@ad<=19991222 and 'copper' and 'TiAlN' and 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:42
-	1	@ad<=19991222 and 'copper' same 'TiAlN' same 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 13:07
-	0	@ad<=19991222 and 'capacitor' with 'BST' with 'TiAlN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:25
-	2	@ad<=19991222 and 'BST' with 'TiAlN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:25

-	8	@ad<=19991222 and 'capacitor' with 'ferroelectric' with 'conductive diffusion barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:04
-	0	@ad<=19991222 and copper near electrode and 'BST' same 'TiAlN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:39
-	3	@ad<=19991222 and copper and 'BST' same 'TiAlN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:39
-	50	@ad<=19991222 and 'Al' and 'TiAlN' and 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:46
-	25	@ad<=19991222 and 'Aluminum' and 'TiAlN' and 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 08:25
-	48	@ad<=19991222 and 'conductive' and 'TiAlN' and 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:58
-	15	@ad<=19991222 and 'stack capacitor' and 'TiAlN' and 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:22
-	2	"20020167086"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/15 12:55
-	8	@ad<=20010508 and 'BST' same 'TiN' same 'aluminum' with 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:02
-	3	@ad<=20010508 and 'high k' same 'TiN' same 'aluminum' with 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:03
-	2	("5990541").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:03
-	5	@ad<=19991222 and 'ferroelectric' same 'barrier' same 'copper' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:08
-	236	@ad<=19991222 and 'ferroelectric' same 'barrier' same 'metal' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:13
-	4	@ad<=19991222 and 'capacitor' same 'ferroelectric' same 'barrier' same 'copper' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:09

-	5	@ad<=19991222 and 'stack capacitor' and 'TiAlN' and 'PZT' and 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:22
-	31	@ad<=19991222 and 'stack capacitor' and 'TiN' and 'PZT' and 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:29
-	2	@ad<=19991222 and 'capacitor' and 'TiN' and 'PZT' and 'copper electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:33
-	3	@ad<=20010508 and 'capacitor' and 'TiN' and 'PZT' and 'copper electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:34
-	283	@ad<=20010508 and 'capacitor' and 'TiN' and 'PZT' and 'al' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:35
-	77	@ad<=20010508 and 'capacitor' same 'electrode' with 'aluminum' same 'barrier' and 'PZT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 07:40
-	15	@ad<=20010508 and 'capacitor' same 'electrode' with 'copper' same 'barrier' and 'PZT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:15
-	3	@ad<=20010508 and 'electrode' with 'conductive barrier' with 'PZT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:19
-	55	@ad<=20010508 and 'electrode' with 'TiN' with 'PZT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:32
-	81	@ad<=20010508 and 'electrode' adj2 'copper' with 'TiN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:33
-	5	@ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'BST'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:45
-	3	@ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'high k'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:45
-	66	@ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'high dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:48
-	3	@ad<=20010508 and 'copper' adj2 'electrode' with 'TiN' and 'high dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 08:49

-	25	@ad<=19991222 and 'ferroelectric' with 'capacitor' and 'TiAlN' and 'metal layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 11:41
-	0	@ad<=19991222 and 'ferroelectric' with 'capacitor' and 'TiAlN' and 'copper electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 09:02
-	1	"5053917".PN.	USPAT	2004/07/01 10:37
-	0	@ad<=19991222 and 'copper' same 'IrO.sub.2' same 'Ir.sub.O.sub3' same 'Ir' and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 11:43
-	4	@ad<=19991222 and 'copper' same 'IrO.sub.2' same 'Ir' and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 11:43
-	2	@ay<=1999 and tang-shaoping.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 14:38
-	6	@ay<=1999 and summerfelt-scott.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 08:38
-	4	@ay<=1999 and crenshaw-darius.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 08:38
-	1	@ay<=1999 and kirlin-peter.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 08:41
-	5	@ay<=1999 and gnade-bruce.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 08:44
-	31	@ay<=1999 and gilbert.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:08
-	5	@ay<=1999 and xing-guoqiang.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 10:59
-	692	@ay<=1999 and 'capacitor' same 'lower electrode' with 'polysilicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:18
-	1	@ay<=1999 and 'capacitor' same 'lower electrode' with 'polysilicon' same 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:19
-	9	@ay<=1999 and 'capacitor' same 'plug' with 'silicon' same 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:24

-	29	@ay<=1999 and 'contact plug' with 'silicon' same 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:25
-	21	@ay<=1999 and 'contact plug' with 'silicon' with 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:37
-	48	@ay<=1999 and 'capacitor' and 'doped' adj1 'silicon' with 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:38
-	76	@ay<=1999 and 'electrode' and 'doped' adj1 'silicon' with 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:38
-	17	@ay<=1999 and 'capacitor' with 'electrode' and 'doped' adj1 'silicon' with 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:51
-	33	@ay<=1999 and 'electrode' same 'doped' adj1 'silicon' with 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:53
-	7	@ay<=1999 and 'capacitor' with 'electrode' same 'doped' adj1 'silicon' with 'copper'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 09:52
-	0	@ay<=1999 and ma-shawing.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 11:00
-	0	@ay<=1999 and ma-shawing.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 11:00
-	0	ma-shawing.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 11:00
-	1	@ay<=1999 and ma-shawming.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 11:01
-	9	ma-shawming.in. and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 11:01
-	18	@ad<=20010508 and 'amorphous BST' and 'perovskite'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/02 13:07